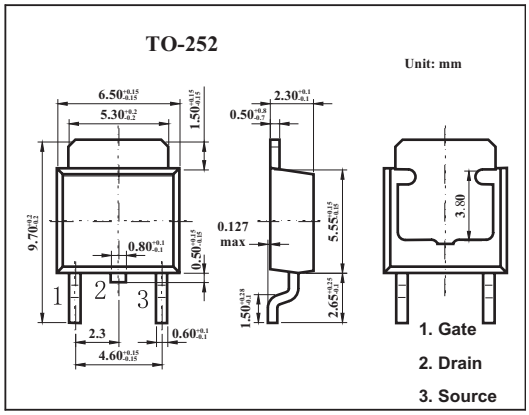
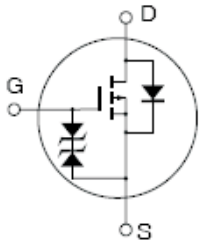
Silicon P-Channel MOS FET

2SJ130S

Features

- Low on-resistance
- High speed switching
- Low drive current
- No secondary breakdown
- Suitable for switching regulator, DC-DC converter and ultrasonic power oscillators





Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Drain to source voltage	V_{DSS}	-300	V
Gate to source voltage	V_{GSS}	±20	V
Drain current	$I_{D(DS)}$	-1	A
Drain peak current	$I_{D(pulse)}$	-2	A
Body to drain diode reverse drain current	I_{DR}	-1	A
Channel dissipation (Tc=25℃)	Pch	20	W
Channel temperature	Tch	150	℃
Storage temperature	T_{stg}	-55 to +150	℃

2SJ130S

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Drain to source breakdown voltage	$V_{(BR)DSS}$	I_D = -10 mA, V_{GS} = 0	-300			V
Gate to source breakdown voltage	$V_{(BR)GSS}$	I_G = ±100 μA, V_{DS} = 0	±20			V
Gate to source leak current	I_{GSS}	V_{GS} = ±16 V, V_{DS} = 0			±10	μA
Zero gate voltage drain current	I_{DSS}	V_{DS} = -240 V, V_{GS} = 0			-100	μA
Gate to source cutoff voltage	$V_{GS(off)}$	I_D = -1 mA, V_{DS} = -10 V	-2		-4	V
Static Drain to source on stateresistance	$R_{DS(on)}$	I_D = -0.5 A, V_{GS} = -10 V		6.0	8.5	Ω
Forward transfer admittance	|yfs|	I_D = -0.5 A, V_{DS} = -20 V	0.25	0.4		S
Input capacitance	C_{iss}	V_{DS} = -10 V, V_{GS} = 0, f = 1 MHz		235		pF
Output capacitance	C_{oss}			65		pF
Reverse transfer capacitance	C_{rss}			16		pF
Turn-on delay time	$t_{d(on)}$	I_D = -0.5 A, V_{GS} = -10 V, R_L = 60 Ω		10		ns
Rise time	t_r			25		ns
Turn-off delay time	$t_{d(off)}$			35		ns
Fall time	t_f			45		ns
Body to drain diode forward voltage	V_{DF}	I_F = -1 A, V_{GS} = 0		-0.9		V
Body to drain diode reverse recovery time	t_{rr}	I_F = -1 A, V_{GS} = 0, diF/dt = 50 A/μs		200		ns